

PLUS Search Results for S/N 10/714,868, Searched August 16, 2005

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6137135	6121089	5282018	5793064	6040600
6040212	5708286	5349224	5796125	6072214
5471075	5747851	5525821	5821580	6075269
5262336	5721148	5581100	5828100	6100140
5283202	5912497	5623152	5945692	6103578
5488236	6060747	5679966	5969378	6147382
5528058	6097063	5714781	5973360	6188109
6031265	6114727	5751024	5977569	6211549
6246092	6137122	5773851	6001678	6221721
5324966	6150671	5773852	6040599	6211549

Most Frequently Occurring Classifications of Patents Returned
From A Search of 10/714,868 on August 16, 2005

Combined Classifications

22 257/E29.201	3 257/E21.385
16 257/330	3 257/E21.417
16 257/331	3 257/E21.418
16 257/E29.26	3 257/E21.42
13 257/341	3 257/E29.015
11 257/139	3 257/E29.118
11 257/E21.419	3 257/E29.131
10 257/E29.067	3 257/E29.198
9 257/E21.384	3 257/E29.261
8 257/E29.028	3 257/E29.262
7 257/133	2 257/119
7 257/329	2 257/124
7 257/378	2 257/132
7 257/E29.013	2 257/137
7 438/270	2 257/140
6 257/334	2 257/143
6 257/401	2 257/144
6 257/E29.066	2 257/156
6 257/E29.257	2 257/212
5 257/138	2 257/263
5 257/147	2 257/337
5 257/339	2 257/397
5 257/E29.214	2 257/501
5 257/E29.259	2 257/502
5 438/138	2 257/577
5 438/268	2 257/77
4 257/141	2 257/E21.137
4 257/153	2 257/E21.341
4 257/328	2 257/E21.614
4 257/332	2 257/E27.016
4 257/343	2 257/E27.026
4 257/347	2 257/E27.06
4 257/E29.2	2 257/E29.182
4 257/E29.216	2 257/E29.195
3 257/142	2 257/E29.197
3 257/333	2 257/E29.199
3 257/342	2 257/E29.256
3 257/E21.033	2 257/E29.258
3 257/E21.218	2 438/139
3 257/E21.345	2 438/238
3 257/E21.346	2 438/589

16 257/330 (8 OR, 8 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/264 ...Enhancement mode or with high resistivity channel (e.g., doping of 10^{15} cm⁻³ or less)
- 257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
- 257/327 ..Short channel insulated gate field effect transistor
- 257/329 ...Gate controls vertical charge flow portion of channel (e.g., VMOS device)
- 257/330Gate electrode in groove

16 257/331 (4 OR, 12 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/264 ...Enhancement mode or with high resistivity channel (e.g., doping of 10^{15} cm⁻³ or less)
- 257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
- 257/327 ..Short channel insulated gate field effect transistor
- 257/329 ...Gate controls vertical charge flow portion of channel (e.g., VMOS device)
- 257/330Gate electrode in groove
- 257/331Plural gate electrodes or grid shaped gate electrode

13 257/341 (2 OR, 11 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/264 ...Enhancement mode or with high resistivity channel (e.g., doping of 10^{15} cm⁻³ or less)
- 257/288 .Having insulated electrode (e.g., MOSFET, MOS diode)
- 257/327 ..Short channel insulated gate field effect transistor
- 257/335 ...Active channel region has a graded dopant concentration decreasing with distance from source region (e.g., double diffused device, DMOS transistor)
- 257/341Plural sections connected in parallel (e.g., power MOSFET)

11 257/139 (5 OR, 6 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/111 ..Triggered by V_{BO} overvoltage means
- 257/133 .Combined with field effect transistor
- 257/139 ..With extended latchup current level (e.g., COMFET device)

7 257/133 (1 OR, 6 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/111 ..Triggered by V_{BO} overvoltage means
- 257/133 .Combined with field effect transistor

7 257/329 (3 OR, 4 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/264 ...Enhancement mode or with high resistivity
channel (e.g., doping of 10^{15} cm⁻³ or less)
- 257/288 .Having insulated electrode (e.g., MOSFET, MOS
diode)
- 257/327 ..Short channel insulated gate field effect
transistor
- 257/329 ...Gate controls vertical charge flow portion
of channel (e.g., VMOS device)

7 257/378 (0 OR, 7 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/264 ...Enhancement mode or with high resistivity
channel (e.g., doping of 10^{15} cm⁻³ or less)
- 257/288 .Having insulated electrode (e.g., MOSFET, MOS
diode)
- 257/368 ..Insulated gate field effect transistor in
integrated circuit
- 257/378 ...Combined with bipolar transistor

7 438/270 (3 OR, 4 XR)

Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS

- 438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION
- OR
- 438/197 .Having insulated gate (e.g., IGFET, MISFET,
MOSFET, etc.)
 - 438/268 ..Vertical channel
 - 438/270 ...Gate electrode in trench or recess in
semiconductor substrate

6 257/334 (1 OR, 5 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/264 ...Enhancement mode or with high resistivity
channel (e.g., doping of 10^{15} cm⁻³ or less)
- 257/288 .Having insulated electrode (e.g., MOSFET, MOS
diode)
- 257/327 ..Short channel insulated gate field effect
transistor
- 257/329 ...Gate controls vertical charge flow portion
of channel (e.g., VMOS device)
- 257/330Gate electrode in groove
- 257/334In integrated circuit structure

6 257/401 (0 OR, 6 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

- 257/264 ...Enhancement mode or with high resistivity
channel (e.g., doping of 10^{15} cm⁻³ or less)
- 257/288 .Having insulated electrode (e.g., MOSFET, MOS
diode)

-
- 257/368 ..Insulated gate field effect transistor in
integrated circuit
- 257/401 ...With specified physical layout (e.g., ring
gate, source/drain regions shared between plural FETs,
plural sections connected in parallel to form power MOSFET)
- 5 257/138 (0 OR, 5 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
- 257/111 ..Triggered by V BO overvoltage means
- 257/133 ..Combined with field effect transistor
- 257/137 ..Having controllable emitter shunt
- 257/138 ...Having gate turn off (GTO) feature
- 5 257/147 (0 OR, 5 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
- 257/111 ..Triggered by V BO overvoltage means
- 257/147 ..With extended latchup current level (e.g.,
gate turn off "GTO" device)
- 5 257/339 (1 OR, 4 XR)
Class 257 : ACTIVE SOLID-STATE DEVICES
- 257/264 ...Enhancement mode or with high resistivity
channel (e.g., doping of 10^{15} cm⁻³ or less)
- 257/288 ..Having insulated electrode (e.g., MOSFET, MOS
diode)
- 257/327 ..Short channel insulated gate field effect
transistor
- 257/335 ...Active channel region has a graded dopant
concentration decreasing with distance from source region
(e.g., double diffused device, DMOS transistor)
- 257/339 With means to increase breakdown voltage
- 5 438/138 (1 OR, 4 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/133 MAKING REGENERATIVE-TYPE SWITCHING DEVICE
(E.G., SCR, IGBT, THYRISTOR, ETC.)
- 438/135 ..Having field effect structure
- 438/138 ..Vertical channel
- 5 438/268 (2 OR, 3 XR)
Class 438 : SEMICONDUCTOR DEVICE MANUFACTURING: PROCESS
- 438/142 MAKING FIELD EFFECT DEVICE HAVING PAIR OF
ACTIVE REGIONS SEPARATED BY GATE STRUCTURE BY FORMATION
- OR
- 438/197 ALTERATION OF SEMICONDUCTIVE ACTIVE REGIONS
..Having insulated gate (e.g., IGFET, MISFET,
MOSFET, etc.)
- 438/268 ..Vertical channel

4 257/141 (1 OR, 3 XR)

Class 257 : ACTIVE SOLID-STATE DEVICES

257/111 ..Triggered by V BO overvoltage means

257/133 .Combined with field effect transistor

257/139 ..With extended latchup current level (e.g.,
COMFET device)

257/141 ...Lateral structure, i.e., current flow
parallel to main device surface